

Ultra-Low Noise Amplifier for Global Navigation Satellite Systems (GNSS)

FEATURES

- Reduce RF environment Interference with patented Smart-Linearity-Technology (SLT);
- low noise figure(NF)=0.85dB@1.575GHz; NF =0.79dB@1.227GHz;NF=0.80dB@1.176GHz;
- High power gain=18.2dB@1.575GHz;power gain=18.9dB@1.227GHz;power gain=18.7dB @1.176 GHz;
- High linearity IIP3oob=+6.5dBm;
- High input 1dB-compression point=-7.6dBm;
- Requires only one input matching inductor;
- RF output internally matched to 50 ohm;
- Supply voltage: 1.5V to 3.6V;
- Operating frequencies: GPS L1、 L2/L5 band;
- DFN 1.5mmX1.0mmX0.55mm-6L package;
- 3KV HBM ESD protection (including RFIN and RFOUT pin);

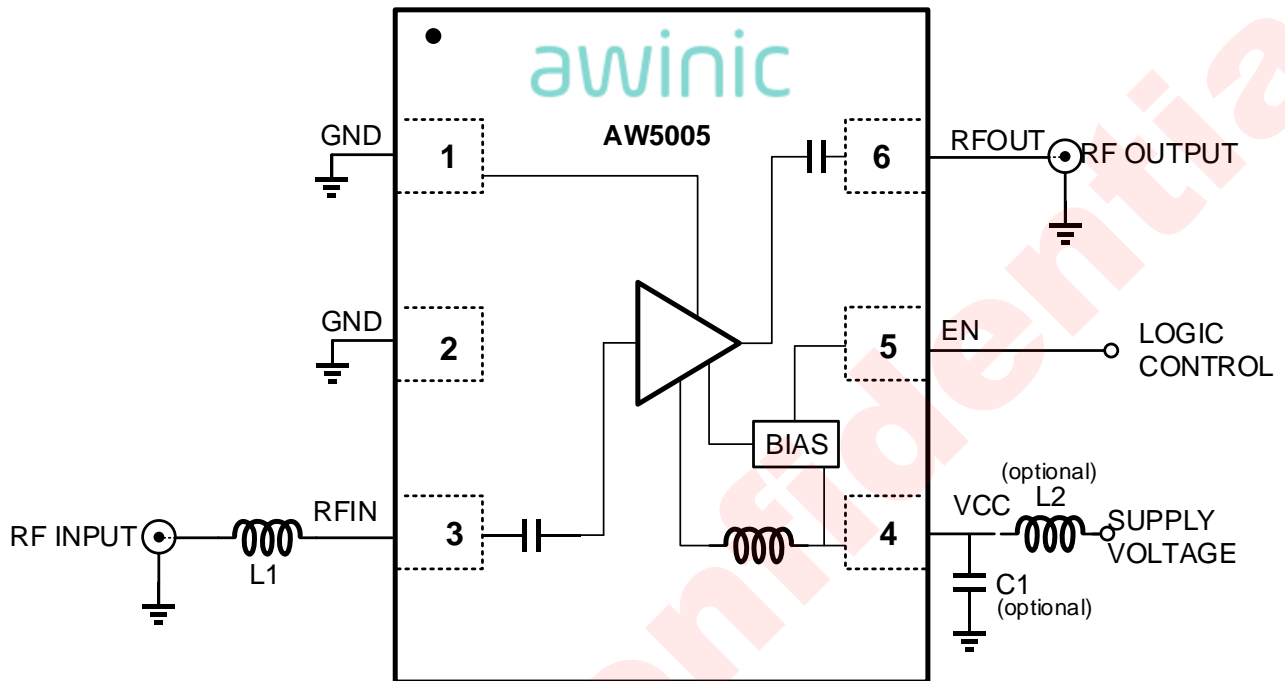
APPLICATIONS

- Smart phones, feature phones;
- Tablet PCs;
- Personal Navigation Devices;
- Digital Still Cameras, Digital Video Cameras;
- RF Front End modules;
- Complete GPS chipset modules;
- Theft protection(laptop, ATM);

GENERAL DESCRIPTION

- The AW5005 is a Low Noise Amplifier designed for Global Navigation Satellite Systems (GNSS) as GPS, GLONASS, Galileo and Compass. With on-chip DC blocking capacitors at RFIN and RFOUT, The AW5005 can be close to the antenna, requires only one external input matching inductor, and reduces assembly complexity and the PCB area, enabling a cost-effective solution.
- The AW5005 with patented Smart Linearity Technology (SLT) achieves ultra-low noise figure, high linearity, high gain, over a wide range of supply voltages from 1.5V up to 3.6V. All these features make AW5005 an excellent choice for GNSS LNA as it improves sensitivity with low noise figure and high gain, provides better immunity against out-of-band jammer signals with high linearity, reduces filtering requirement of preceding stage and hence reduces the overall cost of the GNSS receiver.
- The AW5005 is available in a small lead-free, RoHS-Compliant, DFN 1.5mm X 1.0mm X 0.55mm -6L package.

TYPICAL APPLICATION CIRCUIT



C1, L2 Closed to LNA

Figure 1 Typical Application Circuit of AW5005 for GNSS L1、L2/L5

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PIN CONFIGURATION AND TOP MARK

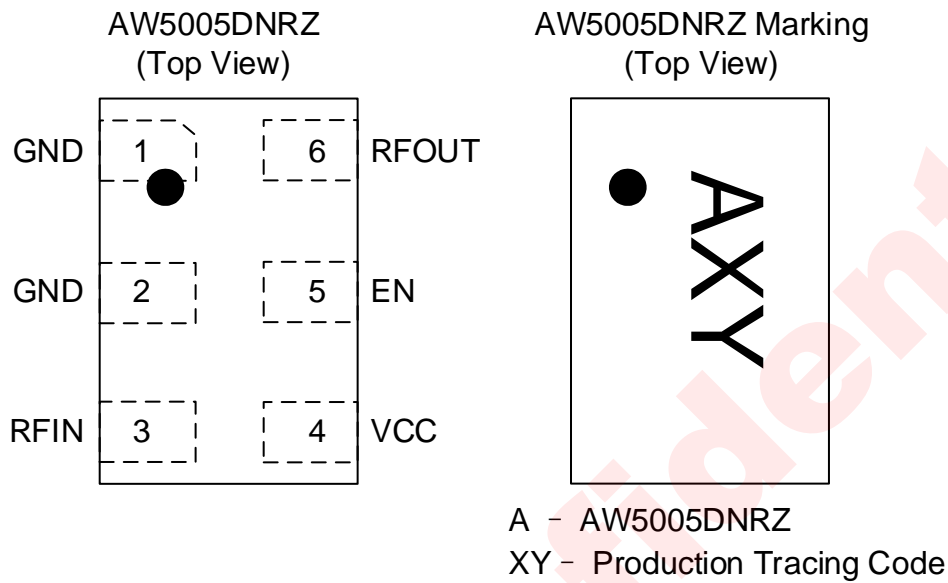
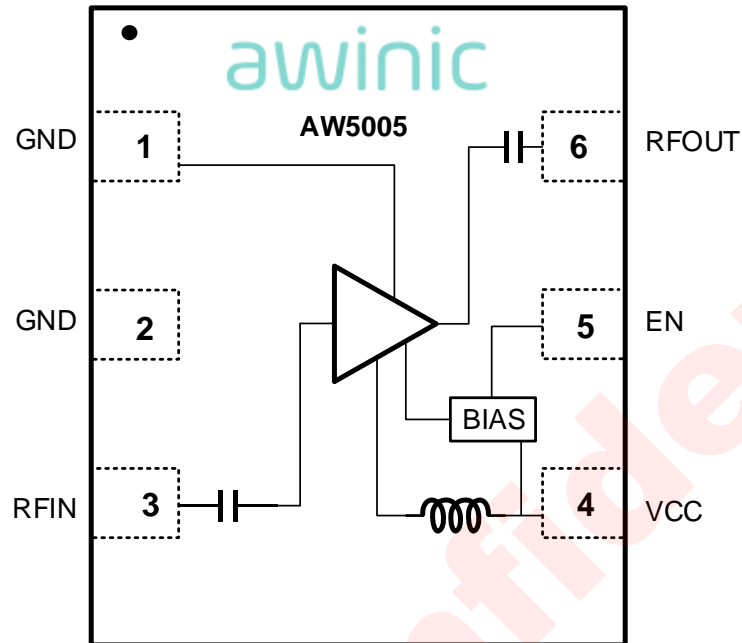


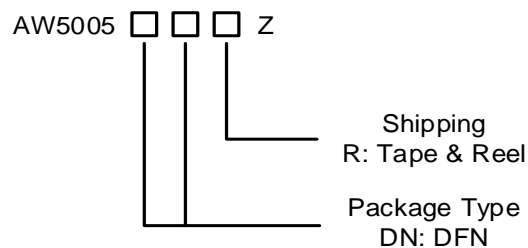
Figure 2 Pin Configuration and Top Mark

PIN DEFINITION

No.	NAME	DESCRIPTION
1	GND	Ground
2	GND	Ground
3	RFIN	LNA input
4	VCC	DC Supply
5	EN	Logic control
6	RFOUT	LNA output

FUNCTIONAL BLOCK DIAGRAM**ORDERING INFORMATION**

Part Number	Temperature	Package	Marking	Moisture Sensitivity Level	Environmental Information	Delivery Form
AW5005DNRZ	-40°C ~ 85°C	DFN 1.5mmX1.0mm- 6L	A	MSL3	ROHS+HF	3000 units/ Tape and Reel



ABSOLUTE MAXIMUM RATINGS^[1]

PARAMETERS	Symbol	Values			
		Min.	Typ.	Max.	
Supply Voltage at pin VCC	V _{CC}	-0.3	-	5	V
Voltage at pin EN [2]	V _{EN}	-0.3	-	5	V
Current into pin VCC	I _{CC}	-	-	30	mA
RF input power [3]	P _{IN}	-	-	10	dBm
Package thermal resistance	θ _{JA}	-	148.2	-	°C/W
Junction temperature	T _J	-	-	150	°C
Storage temperature range	T _{STG}	-65	-	150	°C
Ambient temperature range	T _{amb}	-40	-	85	°C
Solder temperature(10s)		-	260	-	°C
ESD range					
HBM [4]			±3000		V
CDM			±1000		V
Latch-up					
Standard: JEDEC STANDARD NO.78E SEPTEMBER 2016			+IT: +400 -IT: -400		mA

Note1: Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device.

These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute maximum rated conditions for extended periods may affect device reliability.

Note2: Warning: due to internal ESD diode protection, the applied DC voltage should not exceed 5.0V in order to avoid excess current.

Note3: The RF input and RF output are AC coupled through internal DC blocking capacitor.

Note4: HBM standard: MIL-STD-883J Method 3015.9.

ELECTRICAL CHARACTERISTICS

(AW5005 EVB^[1]; VCC=1.5 to 3.6V, TA=-40~+85°C, f=1550MHz to 1615MHz; Typical values are at VCC=2.8V and TA=+25°C, f=1575.42MHz, input matched to 50Ω using a 9.1nH inductor, unless otherwise noted)

PARAMETER		TEST CONDITION	MIN	TYP	MAX	UNIT
DC ELECTRICAL CHARACTERISTICS						
V _{CC}	Supply Voltage		1.5	-	3.6	V
I _{SD}	Shut-Down Current	EN=Low			1	μA
I _{CC}	Supply Current	EN=High		8.0	13.0	mA
V _{EN}	Digital Input-Logic High		0.80			V
V _{EN}	Digital Input-Logic Low				0.45	V
AC ELECTRICAL CHARACTERISTICS						
G _p	Power Gain		16.0	18.2	18.5	dB
RL _{in}	Input Return Loss			5.6		dB
RL _{out}	Output Return Loss			10		dB
ISL	Reverse Isolation		25.0	28.5		dB
NF	Noise Figure ^[2]	Z _s =50 ohm; No jammer		0.85		dB
K _f	Stability factor	f=20MHz...10GHz	1			
NF _j	Noise Figure with jammer	P _{jam} =-20dBm; f _{jam} =850MHz		0.72	1.10	dB
		P _{jam} =-20dBm; f _{jam} =1850MHz		1.14	1.50	dB
IP1dB	Inband input 1dB-compression point	f=1575.42MHz	-9.0	-7.6		dBm
IIP3 _{oob}	Out-of-band input 3 rd -order intercept point	f1=1712.7MHz ^[3] ; f2=1850MHz; Pin=-20dBm;	+4.0	+6.1		dBm
IIP3 _{oob}	Out-of-band input 3 rd -order intercept point	f1=1712.7MHz ^[3] ; f2=1850MHz; Pin=-30dBm;	+4.5	+6.5		dBm
IIP2 _{oob}	Out-of-band input 2 nd -order intercept point	f1=824.6MHz ^[4] ; f2=2400MHz; Pin=-20dBm	-2.0	-1.2		dBm
IIP2 _{oob}	Out-of-band input 2 nd -order intercept point	f1=824.6MHz ^[4] ; f2=2400MHz; Pin=-30dBm	-2.0	-1.2		dBm
H2-input referred	LTE band-13 2 nd Harmonic	f=787.76MHz; Pin=-25dBm;		-74.4	-70.0	dBm

PARAMETER		TEST CONDITION	MIN	TYP	MAX	UNIT
		fH2=1575.52MHz				
t _{on}	turn-on time	time from V _{EN} ON to 90% of the final gain		2.2	2.5	μs
t _{off}	turn-off time	time from V _{EN} OFF to 10% of the gain		1.7	2.0	μs

Note1: input matched to 50 ohm using a high quality-factor 9.1nH inductor.

Note2: 0.08dB PCB losses are subtracted.

Note3: $IIP3=0.5*(Po_{f1}-IM3)+Pi_{f1}$.

Note4: $IIP2=Po_{f2}+Pi_{f2}-IM2$.

(AW5005 EVB^[1]; VCC=1.5 to 3.6V, TA=-40~+85°C, f=1550MHz to 1615MHz; Typical values are at VCC=1.8V and TA=+25°C, f=1575.42MHz, input matched to 50Ω using a 9.1nH inductor, unless otherwise noted)

PARAMETER		TEST CONDITION	MIN	TYP	MAX	UNIT
DC ELECTRICAL CHARACTERISTICS						
V _{CC}	Supply Voltage		1.5	-	3.6	V
I _{SD}	Shut-Down Current	EN=Low			1	μA
I _{CC}	Supply Current	EN=High		6.0	15.0	mA
V _{EN}	Digital Input-Logic High		0.80			V
V _{EN}	Digital Input-Logic Low				0.45	V
AC ELECTRICAL CHARACTERISTICS						
G _p	Power Gain		16.0	17.5	18.0	dB
RL _{in}	Input Return Loss			5.3		dB
RL _{out}	Output Return Loss			10		dB
ISL	Reverse Isolation		25.0	28.0		dB
NF	Noise Figure ^[2]	Z _s =50 ohm; No jammer		0.83		dB
K _f	Stability factor	f=20MHz...10GHz	1			
NF _j	Noise Figure with jammer	P _{jam} =-20dBm; f _{jam} =850MHz		0.76	1.10	dB
		P _{jam} =-20dBm; f _{jam} =1850MHz		1.18	1.50	dB
IP1dB	Inband input 1dB-compression point	f=1575.42MHz	-14.0	-12.5		dBm
IIP3 _{oob}	Out-of-band input 3 rd -order intercept point	f1=1712.7MHz ^[3] ; f2=1850MHz; Pin=-20dBm;	-1.0	0.7		dBm
IIP3 _{oob}	Out-of-band input 3 rd -order intercept point	f1=1712.7MHz ^[3] ; f2=1850MHz; Pin=-30dBm;	0	2.5		dBm
IIP2 _{oob}	Out-of-band input 2 nd -order intercept point	f1=824.6MHz ^[4] ; f2=2400MHz; Pin=-20dBm	-3.0	-1.9		dBm
IIP2 _{oob}	Out-of-band input 2 nd -order intercept point	f1=824.6MHz ^[4] ; f2=2400MHz; Pin=-30dBm	-3.0	-1.7		dBm
H2-input referred	LTE band-13 2 nd Harmonic	f=787.76MHz; Pin=-25dBm; fH2=1575.52MHz		-72.6	-70.0	dBm
t _{on}	turn-on time	time from V _{EN} ON to 90% of the final gain		2.2	2.5	μs

PARAMETER		TEST CONDITION	MIN	TYP	MAX	UNIT
t _{off}	turn-off time	time from V _{EN} OFF to 10% of the gain		1.7	2.0	μs

Note1: input matched to 50 ohm using a high quality-factor 9.1nH inductor.

Note2: 0.08dB PCB losses are subtracted.

Note3: $IIP3=0.5*(Po_{f1}-IM3)+Pi_{f1}$.

Note4: $IIP2=Po_{f2}+Pi_{f2}-IM2$.

(AW5005 EVB^[1]; VCC=1.5 to 3.6V, TA=-40~+85°C, f=1227.60±1.023MHz; Typical values are at VCC=2.8V and TA=+25°C, f=1227.60MHz, input matched to 50Ω using a 15nH inductor, unless otherwise noted)

PARAMETER		TEST CONDITION	MIN	TYP	MAX	UNIT
DC ELECTRICAL CHARACTERISTICS						
V _{CC}	Supply Voltage		1.5	-	3.6	V
I _{SD}	Shut-Down Current	EN=Low			1	μA
I _{CC}	Supply Current	EN=High		8	13.0	mA
V _{EN}	Digital Input-Logic High		0.80			V
V _{EN}	Digital Input-Logic Low				0.45	V
AC ELECTRICAL CHARACTERISTICS						
G _p	Power Gain		16.0	18.9	18.5	dB
RL _{in}	Input Return Loss			5.5		dB
RL _{out}	Output Return Loss			12.3		dB
ISL	Reverse Isolation		25.0	26.2		dB
NF	Noise Figure ^[2]	Z _s =50 ohm; No jammer		0.79		dB
K _f	Stability factor	f=20MHz...10GHz	1			
NF _j	Noise Figure with jammer	P _{jam} =-20dBm; f _{jam} =850MHz		0.72	1.10	dB
		P _{jam} =-20dBm; f _{jam} =1850MHz		1.14	1.50	dB
IP1dB	Inband input 1dB-compression point	f=1575.42MHz	-9.0	-7.6		dBm
IIP3 _{oob}	Out-of-band input 3 rd -order intercept point	f1=1712.7MHz ^[3] ; f2=1850MHz; Pin=-20dBm;	+4.0	+6.1		dBm
IIP3 _{oob}	Out-of-band input	f1=1712.7MHz ^[3] ; f2=1850MHz;	+4.5	+6.5		dBm

PARAMETER		TEST CONDITION	MIN	TYP	MAX	UNIT
	3 rd -order intercept point	Pin=-30dBm;				
IIP2 _{oob}	Out-of-band input 2 nd -order intercept point	f1=824.6MHz ^[4] ; f2=2400MHz; Pin=-20dBm	-2.0	-1.2		dBm
IIP2 _{oob}	Out-of-band input 2 nd -order intercept point	f1=824.6MHz ^[4] ; f2=2400MHz; Pin=-30dBm	-2.0	-1.2		dBm
H2-input referred	LTE band-13 2 nd Harmonic	f=787.76MHz; Pin=-25dBm; fH2=1575.52MHz		-74.4	-70.0	dBm
t _{on}	turn-on time	time from V _{EN} ON to 90% of the final gain		2.2	2.5	μs
t _{off}	turn-off time	time from V _{EN} OFF to 10% of the gain		1.7	2.0	μs

Note1: input matched to 50 ohm using a high quality-factor 9.1nH inductor.

Note2: 0.08dB PCB losses are subtracted.

Note3: $IIP3=0.5*(Po_{f1-IM3})+Pi_{f1}$.

Note4: $IIP2=Po_{f2}+Pi_{f2}-IM2$.

(AW5005 EVB^[1]; VCC=1.5 to 3.6V, TA=-40~+85°C, f=1227.60±1.023MHz; Typical values are at VCC=1.8V and TA=+25°C, f=1227.60MHz, input matched to 50Ω using a 15nH inductor, unless otherwise noted)

PARAMETER		TEST CONDITION	MIN	TYP	MAX	UNIT
DC ELECTRICAL CHARACTERISTICS						
V _{CC}	Supply Voltage		1.5	-	3.6	V
I _{SD}	Shut-Down Current	EN=Low			1	μA
I _{CC}	Supply Current	EN=High		6.0	13.0	mA
V _{EN}	Digital Input-Logic High		0.80			V
V _{EN}	Digital Input-Logic Low				0.45	V
AC ELECTRICAL CHARACTERISTICS						
G _p	Power Gain		16.0	18.2	18.5	dB
RL _{in}	Input Return Loss			5.4		dB
RL _{out}	Output Return Loss			12.4		dB
ISL	Reverse Isolation		25.0	25.6		dB
NF	Noise Figure ^[2]	Zs=50 ohm; No jammer		0.83		dB
Kf	Stability factor	f=20MHz...10GHz	1			

PARAMETER		TEST CONDITION	MIN	TYP	MAX	UNIT
NF _j	Noise Figure with jammer	P _{jam} =-20dBm; f _{jam} =850MHz		0.72	1.10	dB
		P _{jam} =-20dBm; f _{jam} = 1850MHz		1.14	1.50	dB
IP1dB	Inband input 1dB-compression point	f=1575.42MHz	-9.0	-7.6		dBm
IIP3 _{oob}	Out-of-band input 3 rd -order intercept point	f1=1712.7MHz ^[3] ; f2=1850MHz; Pin=-20dBm;	+4.0	+6.1		dBm
IIP3 _{oob}	Out-of-band input 3 rd -order intercept point	f1=1712.7MHz ^[3] ; f2=1850MHz; Pin=-30dBm;	+4.5	+6.5		dBm
IIP2 _{oob}	Out-of-band input 2 nd -order intercept point	f1=824.6MHz ^[4] ; f2=2400MHz; Pin=-20dBm	-2.0	-1.2		dBm
IIP2 _{oob}	Out-of-band input 2 nd -order intercept point	f1=824.6MHz ^[4] ; f2=2400MHz; Pin=-30dBm	-2.0	-1.2		dBm
H2-input referred	LTE band-13 2 nd Harmonic	f=787.76MHz; Pin=-25dBm; fH2=1575.52MHz		-74.4	-70.0	dBm
t _{on}	turn-on time	time from V _{EN} ON to 90% of the final gain		2.2	2.5	μs
t _{off}	turn-off time	time from V _{EN} OFF to 10% of the gain		1.7	2.0	μs

Note1: input matched to 50 ohm using a high quality-factor 9.1nH inductor.

Note2: 0.08dB PCB losses are subtracted.

Note3: $IIP3=0.5*(Po_{f1-IM3})+Pi_{f1}$.

Note4: $IIP2=Po_{f2}+Pi_{f2}-IM2$.

(AW5005 EVB^[1]; VCC=1.5 to 3.6V, TA=-40~+85°C, f=1176.45±1.023MHz; Typical values are at VCC=2.8V and TA=+25°C, f=1176.45MHz, input matched to 50Ω using a 15nH inductor, unless otherwise noted)

PARAMETER		TEST CONDITION	MIN	TYP	MAX	UNIT
DC ELECTRICAL CHARACTERISTICS						
V _{CC}	Supply Voltage		1.5	-	3.6	V
I _{SD}	Shut-Down Current	EN=Low			1	μA
I _{CC}	Supply Current	EN=High		8.0	13.0	mA

PARAMETER		TEST CONDITION	MIN	TYP	MAX	UNIT
V _{EN}	Digital Input-Logic High		0.80			V
V _{EN}	Digital Input-Logic Low				0.45	V
AC ELECTRICAL CHARACTERISTICS						
G _p	Power Gain		16.0	18.7	18.9	dB
RL _{in}	Input Return Loss			4.9		dB
RL _{out}	Output Return Loss		12.0	14.3		dB
ISL	Reverse Isolation		25.0	26.0		dB
NF	Noise Figure ^[2]	Z _s =50 ohm; No jammer		0.80		dB
K _f	Stability factor	f=20MHz...10GHz	1			
NF _j	Noise Figure with jammer	P _{jam} =-20dBm; f _{jam} =850MHz		0.72	1.10	dB
		P _{jam} =-20dBm; f _{jam} =1850MHz		1.14	1.50	dB
IP1dB	Inband input 1dB-compression point	f=1575.42MHz	-9.0	-7.6		dBm
IIP3 _{oob}	Out-of-band input 3 rd -order intercept point	f1=1712.7MHz ^[3] ; f2=1850MHz; Pin=-20dBm;	+4.0	+6.1		dBm
IIP3 _{oob}	Out-of-band input 3 rd -order intercept point	f1=1712.7MHz ^[3] ; f2=1850MHz; Pin=-30dBm;	+4.5	+6.5		dBm
IIP2 _{oob}	Out-of-band input 2 nd -order intercept point	f1=824.6MHz ^[4] ; f2=2400MHz; Pin=-20dBm	-2.0	-1.2		dBm
IIP2 _{oob}	Out-of-band input 2 nd -order intercept point	f1=824.6MHz ^[4] ; f2=2400MHz; Pin=-30dBm	-2.0	-1.2		dBm
H2-input referred	LTE band-13 2 nd Harmonic	f=787.76MHz; Pin=-25dBm; fH2=1575.52MHz		-74.4	-70.0	dBm
t _{on}	turn-on time	time from V _{EN} ON to 90% of the final gain		2.2	2.5	μs
t _{off}	turn-off time	time from V _{EN} OFF to 10% of the gain		1.7	2.0	μs

Note1: input matched to 50 ohm using a high quality-factor 9.1nH inductor.

Note2: 0.08dB PCB losses are subtracted.

Note3: $IIP3=0.5*(Po_{f1}-IM3)+Pi_{f1}$.

Note4: $IIP2=Po_{f2}+Pi_{f2}-IM2$.

(AW5005 EVB^[1]; VCC=1.5 to 3.6V, TA=-40~+85°C, f=1176.45±1.023MHz; Typical values are at VCC=1.8V and TA=+25°C, f=1176.45MHz, input matched to 50Ω using a 15nH inductor, unless otherwise noted)

PARAMETER		TEST CONDITION	MIN	TYP	MAX	UNIT
DC ELECTRICAL CHARACTERISTICS						
V _{CC}	Supply Voltage		1.5	-	3.6	V
I _{SD}	Shut-Down Current	EN=Low			1	μA
I _{CC}	Supply Current	EN=High		6.0	13.0	mA
V _{EN}	Digital Input-Logic High		0.80			V
V _{EN}	Digital Input-Logic Low				0.45	V
AC ELECTRICAL CHARACTERISTICS						
G _p	Power Gain		16.0	18.0	18.7	dB
RL _{in}	Input Return Loss			5.2		dB
RL _{out}	Output Return Loss		12.0	14.2		dB
ISL	Reverse Isolation		25.0	25.4		dB
NF	Noise Figure ^[2]	Z _s =50 ohm; No jammer		0.84		dB
K _f	Stability factor	f=20MHz...10GHz	1			
NF _j	Noise Figure with jammer	P _{jam} =-20dBm; f _{jam} =850MHz		0.72	1.10	dB
		P _{jam} =-20dBm; f _{jam} =1850MHz		1.14	1.50	dB
IP1dB	Inband input 1dB-compression point	f=1575.42MHz	-9.0	-7.6		dBm
IIP3 _{oob}	Out-of-band input 3 rd -order intercept point	f1=1712.7MHz ^[3] ; f2=1850MHz; Pin=-20dBm;	+4.0	+6.1		dBm
IIP3 _{oob}	Out-of-band input 3 rd -order intercept point	f1=1712.7MHz ^[3] ; f2=1850MHz; Pin=-30dBm;	+4.5	+6.5		dBm
IIP2 _{oob}	Out-of-band input 2 nd -order intercept point	f1=824.6MHz ^[4] ; f2=2400MHz; Pin=-20dBm	-2.0	-1.2		dBm
IIP2 _{oob}	Out-of-band input 2 nd -order intercept point	f1=824.6MHz ^[4] ; f2=2400MHz; Pin=-30dBm	-2.0	-1.2		dBm
H2-input referred	LTE band-13 2 nd Harmonic	f=787.76MHz; Pin=-25dBm; fH2=1575.52MHz		-74.4	-70.0	dBm
t _{on}	turn-on time	time from V _{EN} ON to 90% of the final gain		2.2	2.5	μs

PARAMETER		TEST CONDITION	MIN	TYP	MAX	UNIT
t _{off}	turn-off time	time from V _{EN} OFF to 10% of the gain		1.7	2.0	μs

Note1: input matched to 50 ohm using a high quality-factor 9.1nH inductor.

Note2: 0.08dB PCB losses are subtracted.

Note3: $IIP3=0.5*(Po_{f1}-IM3)+Pi_{f1}$.

Note4: $IIP2=Po_{f2}+Pi_{f2}-IM2$.

APPLICATION BOARD

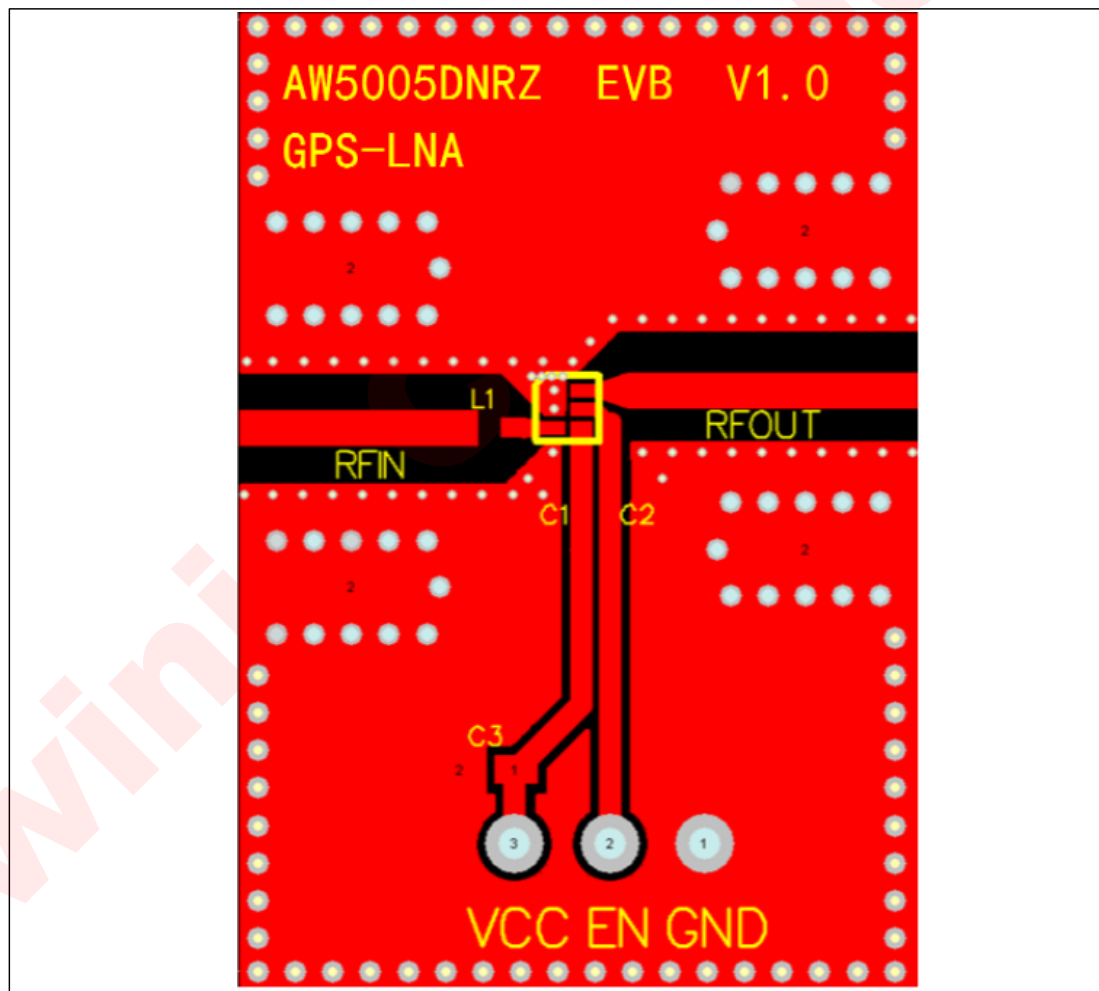


Figure 3. Drawing of Application Board

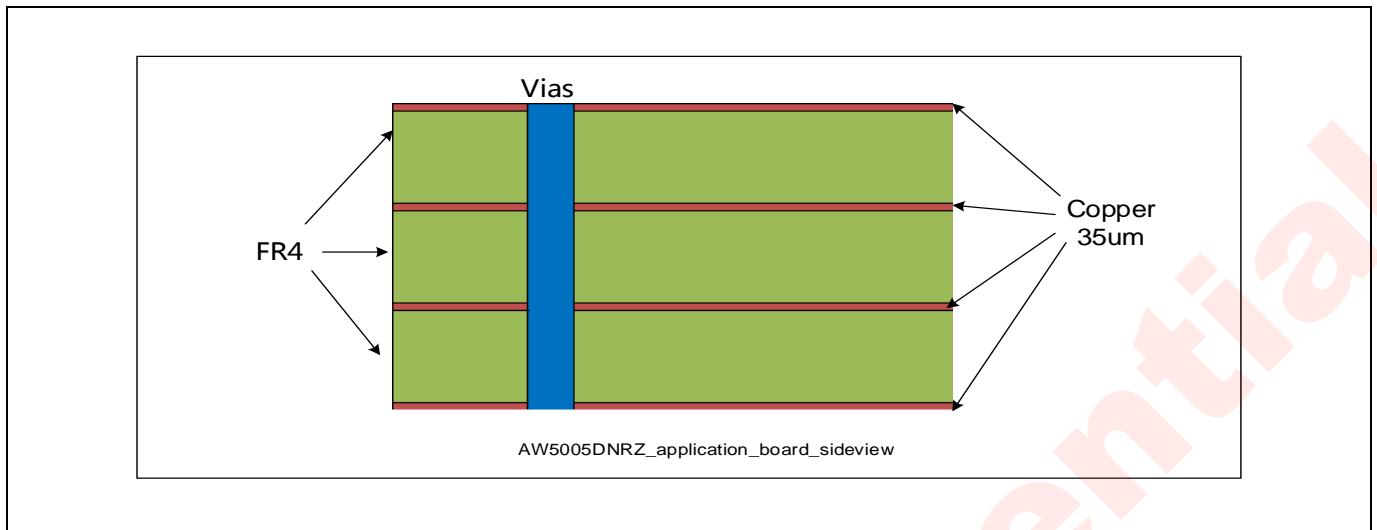
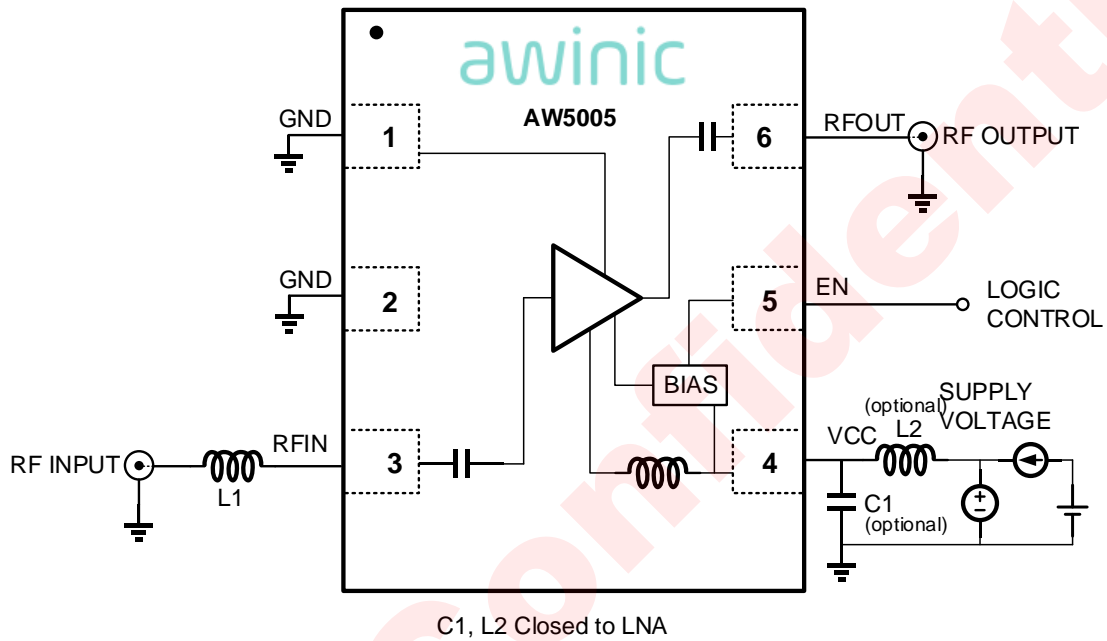


Figure 4. Application Board Cross-Section

TEST CIRCUITS

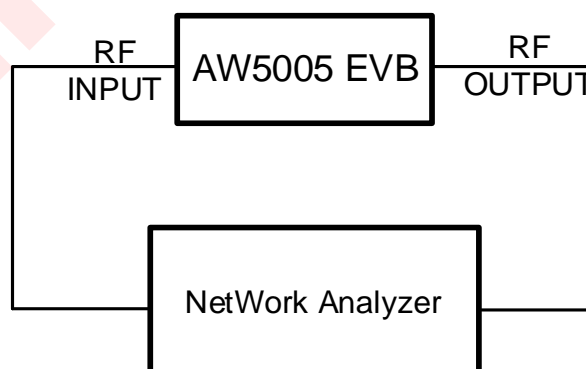
DC Characteristics

The following is the test bench for power supply, pin voltage, supply current, standby current



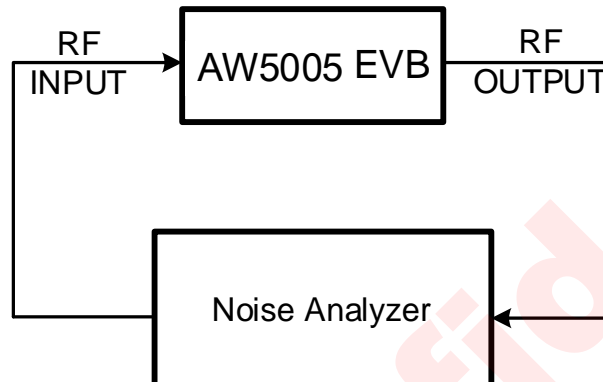
S Parameter

The following is the test bench for input return loss, output return loss, reverse isolation, forward gain, and 1dB gain compression.



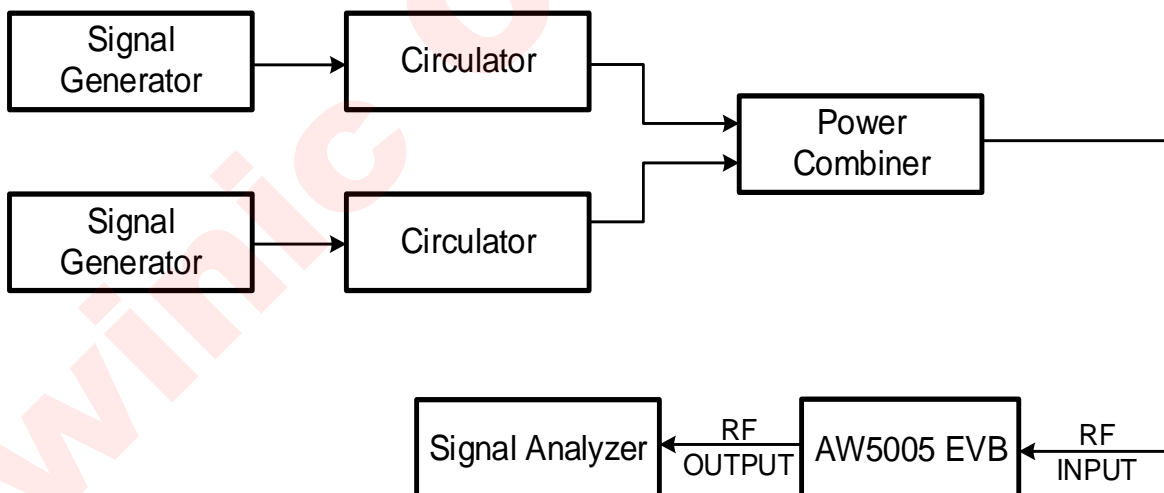
Noise Figure

The following is the test bench for noise figure, power gain.



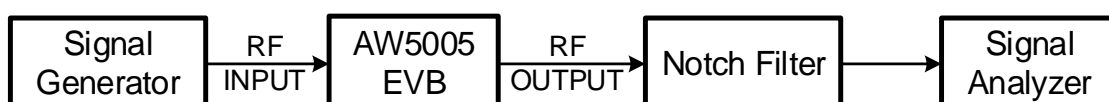
Intermodulation distortion

The following is the test bench for third-order intercept point and second-order intercept point.



Harmonic distortion

The following is the test bench for second-order harmonic distortion.



RECOMMENDED COMPONENTS LIST

Table1 lists the recommended inductor types and values; Table 2 lists the recommended capacitor types and values.

Table1: list of inductor for GNSS L1

Component	Part Number	Inductance	Q(min)	Q Test Frequency	Supplier	Size
	Units	nH		MHz		
L1	LQW15A	9.1	25	250	Murata	0402
L1	SDWL1005C	9.1	24	250	Sunlord	0402
L2	LQW15A	100	20	150	Murata	0402

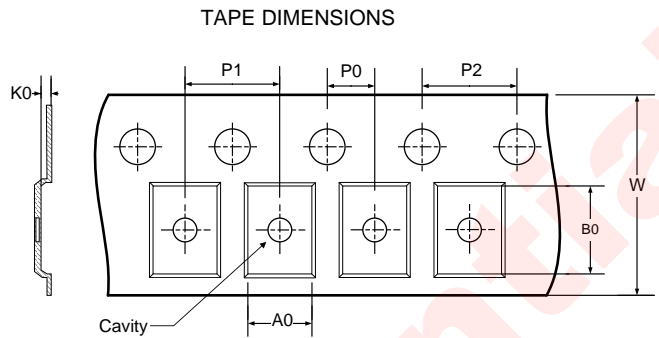
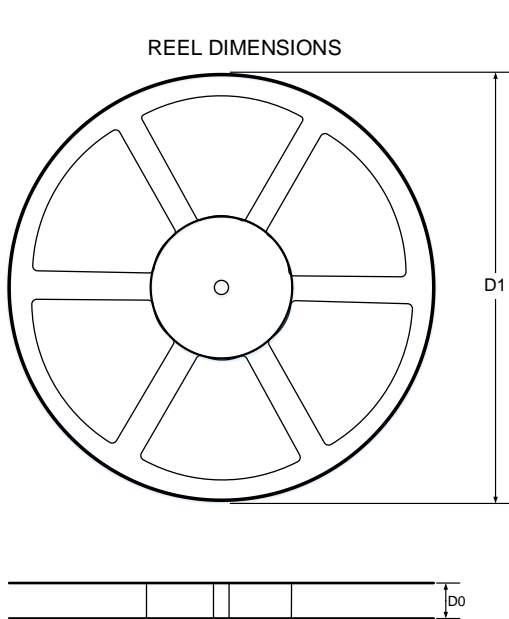
Table2: list of capacitor

Component	Part Number	Capacitance	Rated Voltage	Supplier	Size
	Units	pF	V		
C1	GRM155	1000	50	Murata	0402

PCB LAYOUT CONSIDERATION

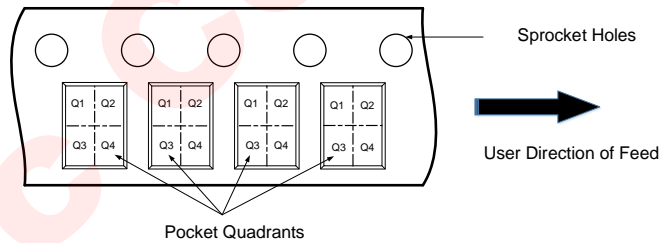
1. The AW5005 requires only one external inductor for input matching. If the device/phone manufacturers implement very good power supply filtering on their boards, the bypass capacitor mentioned in this application circuit may be optional. With the capacitor we can get better performance like a little higher gain etc. The value is optimized for the best gain, noise figure, return loss performance. Typical value of inductor is 9.1nH, capacitor is 1nF. For schematics see Figure1.
2. The output of AW5005 is internally matched to 50 ohm and a DC blocking capacitor is integrated on-chip, thus no external component is required at the output.
3. The AW5005 should be placed close to the GPS antenna with the input-matching inductor. Use 50 ohm micro strip lines to connect RF INPUT and RF OUTPUT. Bypass capacitor should be located close to the device. For long VCC lines, it may be necessary to add more decoupling capacitors. Proper grounding of the GND pins is very important.

TAPE AND REEL INFORMATION



- A0: Dimension designed to accommodate the component width
- B0: Dimension designed to accommodate the component length
- K0: Dimension designed to accommodate the component thickness
- W: Overall width of the carrier tape
- P0: Pitch between successive cavity centers and sprocket hole
- P1: Pitch between successive cavity centers
- P2: Pitch between sprocket hole
- D1: Reel Diameter
- D0: Reel Width

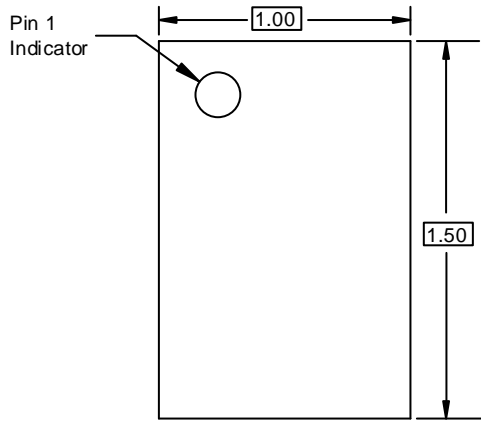
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



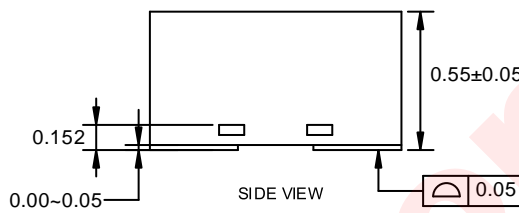
All Dimensions are nominal

D1 (mm)	D0 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P0 (mm)	P1 (mm)	P2 (mm)	W (mm)	Pin1 Quadrant
178	8.4	1.12	1.72	0.7	2	4	4	8	Q1

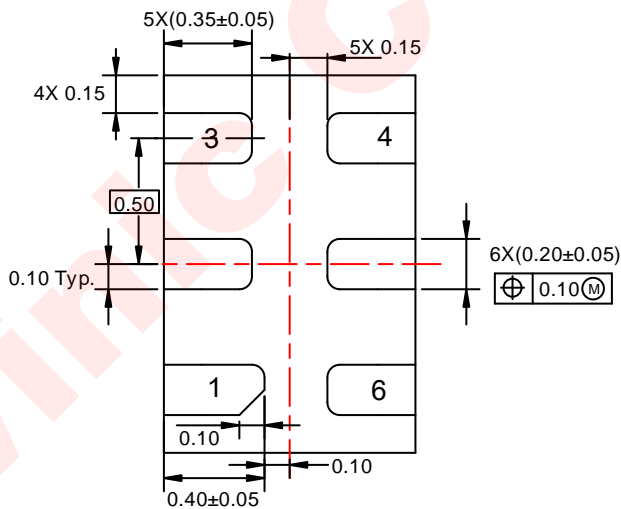
PACKAGE DESCRIPTION



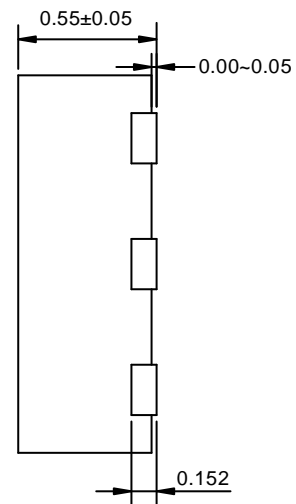
TOP VIEW



SIDE VIEW



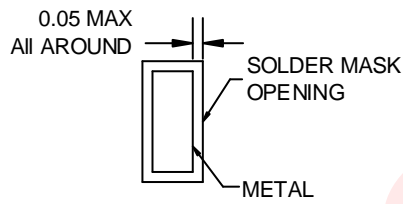
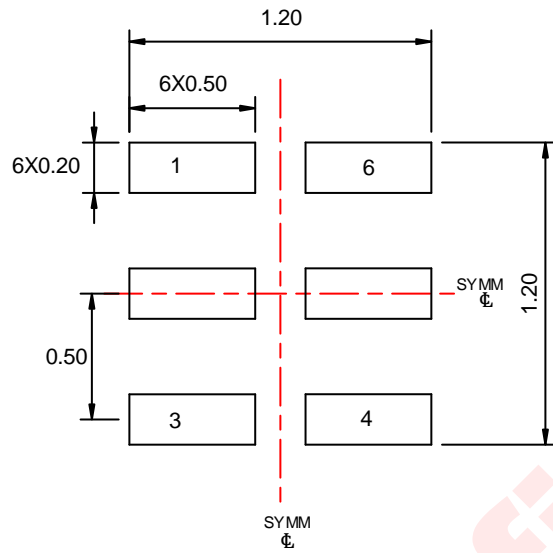
BOTTOM VIEW



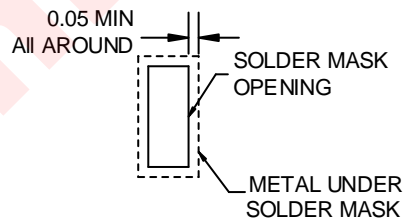
SIDE VIEW

Unit: mm

LAND PATTERN DATA



NON SOLDER MASK DEFINED



SOLDER MASK DEFINED

Unit: mm

REVISION HISTORY

Document ID	Release date	Change Record
AW5005_V1.4	2019-5	● Updated S11 AND S22 OF L1 BAND
AW5005_V1.3	2019-5	● Updated SP AND NF OF L1/L2/L5 BAND
AW5005_V1.2	2019-5	● Updated S21 OF L1 BAND ● Added S21 AND NF OF L2/L5 BAND
AW5005_V1.1	2019-2	● Updated TAPE AND REEL INFORMATION ● Updated PACKAGE DESCRIPTION ● Updated LAND PATTERN DATA ● Updated the Awinic logo
AW5005_V1.0	2016-12	Officially Released

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